PRODUCT / PROCESS CHANGE INFORMATION

1. PCI basic data

1.1 Company	STMicroelectronics International N.V
1.2 PCI No.	ADG/18/10949
1.3 Title of PCI	STD5N60DM2 Datasheet UPDATE
1.4 Product Category	Power MOSFET
1.5 Issue date	2018-06-11

2. PCI Team

2.1 Contact supplier	
2.1.1 Name	ROBERTSON HEATHER
2.1.2 Phone	+1 8475853058
2.1.3 Email	heather.robertson@st.com
2.2 Change responsibility	
2.2.1 Product Manager	Maurizio GIUDICE
2.1.2 Marketing Manager	Anna MOTTESE
2.1.3 Quality Manager	Vincenzo MILITANO

3. Change

3.1 Category	3.2 Type of change	3.3 Manufacturing Location
General Product & Design	Modification of datasheet : Errata/error fix	ASE-WEIHAI (China)

4. Description of change

	Old	New
4.1 Description	IAR=1.7A, Ciss=375pF, Coss=13pF, Crss=0.3pF, Coss eq.=21pF, RG=6.5?, QG=8.6nC, Qgs=2nC, Qgd=5.2nC.	IAR=1A, Ciss=214pF, Coss=12pF, Crss=3.5pF, Coss eq.=21pF, RG=6.5?, QG=5.3nC, Qgs=1.4nC, Qgd=2.7nC.
4.2 Anticipated Impact on form,fit, function, quality, reliability or processability?	no impact	

5. Reason / motivation for change

5.1 Motivation	Improve Service to Customer.
5.2 Customer Benefit	SERVICE IMPROVEMENT

6. Marking of parts / traceability of change

6.1 Description	by traceability code

7. Timing / schedule

7.1 Date of qualification results	2018-06-07
7.2 Intended start of delivery	2018-07-07
7.3 Qualification sample available?	Not Applicable

8. Qualification / Validation

8.1 Description			
8.2 Qualification report and qualification results	In progress	**Issue Date**	

9. Attachments (additional documentations)

10949 Public product.pdf
10949 STD5N60DM2 - Datasheet UPDATE.pdf

10. Affected parts		
10. 1 Current		10.2 New (if applicable)
10.1.1 Customer Part No	10.1.2 Supplier Part No	10.1.2 Supplier Part No
	STD5N60DM2	

Automotive and Discrete Group (ADG)
Power Transistor Division
HV Business Unit

STD5N60DM2 datasheet UPDATE

Dear Customer,

Please be informed that, we are going to modify the datasheet of **STD5N60DM2** according to the following tables:

Table 4: Avalanche characteristics

Symbol	Parameter	Value		Unit
		Current	NEW	
I_{AR} (1)	Avalanche current, repetitive or not repetitive	1.7	1	A

Notes:
(1) Pulse width limited by Tjmax.

Table 6: Dynamic

Symbol	Parameter	Value	Min.	Typ.		Max.	Unit
				Current	NEW		
C_{iss}	Input capacitance	VDS = 100 V, f = 1 MHz, VGS = 0 V	-	375	214	-	pF
C_{oss}	Output capacitance		-	13	12	-	
C_{rss}	Reverse transfer capacitance		-	0.3	3.5	-	
$C_{oss\ eq.}$ (1)	Equivalent output capacitance	VDS = 0 to 480 V, VGS = 0 V	-	21	21	-	pF
R_G	Intrinsic gate resistance	f = 1 MHz, ID = 0 A	-	6.5	6.5	-	Ω
Q_G	Total gate charge	VDD = 480 V, ID = 3.5 A, VGS = 0 to 10 V (see *Figure 15: "Test circuit for gate charge behavior"*)	-	8.6	5.3	-	nC
Q_{gs}	Gate-source charge		-	2	1.4	-	
Q_{gd}	Gate-drain charge		-	5.2	2.7	-	

Notes:
(1) Coss eq. is defined as a constant equivalent capacitance giving the same charging time as Coss when VDS increases from 0 to 80% VDSS.

The change will also have an impact on the related curves.

Please contact us for more information.

Sincerely Yours.

Public Products List

Publict Products are off the shelf products. They are not dedicated to specific customers, they are available through ST Sales team, or Distributors, and visible on ST.com

PCI Title : STD5N60DM2 Datasheet UPDATE
PCI Reference : ADG/18/10949

Subject : Public Products List

Dear Customer,

Please find below the Standard Public Products List impacted by the change.

STD5N60DM2		

IMPORTANT NOTICE – PLEASE READ CAREFULLY